

Electronic states
in
ideal free standing InSb

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Abstract

Exact and general results on the electronic states in ideal free standing In s bounded between $z_3 a_3$ and $(z_3 + N_3) a_3$ – here a_3 is the only primitive vector out of the In plane, z_3 is the bottom boundary and N_3 is a positive integer indicating the thickness of the In – are presented. In many interesting cases, such as in FCC (001) In s and in FCC (110) In s, the energies of most electronic states in the In can be analytically obtained from the corresponding energy band structure of the bulk: For each energy band of the bulk and each two-dimensional wavevector \hat{k} in the In plane, there are $N_3 - 1$ electronic states in the In whose energy is dependent on the In thickness N_3 but not on the In boundary z_3 and maps the energy band of the bulk exactly and one electronic state whose energy is dependent on z_3 but not on N_3 and is above or at the highest energy in that energy band with that \hat{k} . This approach can be further extended to obtain exact and general results on electronic states in quantum wires and quantum dots.

PACS numbers: 73.22.-f, 73.20.-r, 73.21.-b, 73.90.+f

Bloch theorem has been playing a central role in our current understanding on the electronic structures of crystals in modern solid state physics. However, any real crystal always has a finite size and does not have the translational invariance on which Bloch theorem is based. A clear understanding of the properties of electronic states in real crystals of finite size has both theoretical and practical significant importance. Nevertheless, the lack of translational invariance has been a major obstacle in obtaining exact and general results on the electronic states in crystals of finite size. Thus most previous theoretical investigations on the electronic structure of finite crystals were based on approximate and/or numerical approaches and were usually on a specific material and/or based on a specific model[1]. Recently the author obtained exact results on the electronic states in ideal general one dimensional crystals bounded at $x=0$ and $x=L$ - where L is a real number and L is a length equal to a positive integer times of the potential period a - by using a differential equation theory approach [2, 3, 4]. One of the major results of [2] is that the electronic states in one dimensional crystals of finite length can be classified as L -dependent or a -dependent - the energy of the electronic state is dependent on either the length of the crystal L or the crystal boundary a . It also shows that the obstacle due to the lack of translational invariance in one dimensional finite crystals in fact can be circumvented. The basis of [2] is a clear understanding of the zeros of solutions of ordinary differential equations with periodic coefficients obtained by mathematicians[4]. Now we extend our investigations into the three dimensional cases. In this work, we treat the simplest case - the electronic states in ideal free standing films.

The most significant difference between the problem treated in this work and [2] is, the corresponding Schrodinger equation for the electronic states in films is a partial differential equation and thus the problem is now a more difficult one. Furthermore, for the zeros of solutions of three dimensional partial differential equation with periodic coefficients, much less was understood. Nevertheless, based on the results of a new eigenvalue problem - an extension of a mathematical theorem in [4] - we demonstrate that in many interesting cases exact and general results on how the eigenvalues of electronic states in ideal free standing films depend on the thickness can be analytically obtained, many eigenvalues can be directly obtained from the energy band structure of the bulk. A gain, the major obstacle due to the lack of translational invariance can be circumvented.

We will mainly be interested in InS with face-center cubic (FCC) lattices, including diamond structure and zinc-blend structure.

The Schrodinger equation for three dimensional crystals can be written as

$$-\nabla^2 \psi(\mathbf{x}) + v(\mathbf{x}) \psi(\mathbf{x}) = 0; \quad (1)$$

where

$$v(\mathbf{x} + \mathbf{a}_1) = v(\mathbf{x}); \quad v(\mathbf{x} + \mathbf{a}_2) = v(\mathbf{x}); \quad v(\mathbf{x} + \mathbf{a}_3) = v(\mathbf{x});$$

$\mathbf{a}_1, \mathbf{a}_2$ and \mathbf{a}_3 are three primitive vectors of the crystal. The corresponding primitive vectors in k space are denoted as $\mathbf{b}_1, \mathbf{b}_2$ and \mathbf{b}_3 and $\mathbf{a}_i \cdot \mathbf{b}_j = \delta_{ij}$. The position vector \mathbf{x} can be written as $\mathbf{x} = x_1 \mathbf{a}_1 + x_2 \mathbf{a}_2 + x_3 \mathbf{a}_3$ and the k vector as $\mathbf{k} = k_1 \mathbf{b}_1 + k_2 \mathbf{b}_2 + k_3 \mathbf{b}_3$.

The eigenfunctions of (1) satisfying the condition

$$\psi(\mathbf{k}; \mathbf{x} + \mathbf{a}_i) = \psi(\mathbf{k}; \mathbf{x}) \exp(ik_i) \quad k_i < k_i \quad i = 1; 2; 3 \quad (2)$$

are three dimensional Bloch functions. In this work the three dimensional Bloch functions and the energy bands are denoted as $\psi_n(\mathbf{k}; \mathbf{x})$ and $E_n(\mathbf{k})$: $E_0(\mathbf{k}) \quad E_1(\mathbf{k}) \quad E_2(\mathbf{k}) \quad \dots$. The energy band structure in the Cartesian system is denoted as $E_n(k_x; k_y; k_z)$.

For the electronic states in ideal free standing InS we assume that the atomic positions in the InS are the same as in the bulk, the potential $v(\mathbf{x})$ inside the InS is the same as in (1) and all the electronic states are confined in the InS . We choose primitive vectors \mathbf{a}_1 and \mathbf{a}_2 in the InS plane and use $\hat{\mathbf{k}}$ to express the two dimensional wavevector: $\hat{\mathbf{k}} = \hat{k}_1 \hat{\mathbf{b}}_1 + \hat{k}_2 \hat{\mathbf{b}}_2$. $\hat{\mathbf{b}}_1$ and $\hat{\mathbf{b}}_2$ are in the InS plane and $\hat{\mathbf{a}}_i \cdot \hat{\mathbf{b}}_j = \delta_{ij}$.

Suppose A is a parallelogram which has \mathbf{a}_1 forming the sides which meet at a corner and has the bottom defined by $-\mathbf{a}_3$ [5]. The function set $\hat{\psi}(\hat{\mathbf{k}}; \mathbf{x}; -\mathbf{a}_3)$ is defined by the condition

$$\begin{aligned} \hat{\psi}(\hat{\mathbf{k}}; \mathbf{x} + \mathbf{a}_i; -\mathbf{a}_3) &= \hat{\psi}(\hat{\mathbf{k}}; \mathbf{x}; -\mathbf{a}_3) \exp(ik_i) \quad k_i < k_i \quad i = 1; 2 \\ \hat{\psi}(\hat{\mathbf{k}}; \mathbf{x}; -\mathbf{a}_3) &= 0 \quad \text{if } \mathbf{x} \notin A \end{aligned} \quad (3)$$

here A means two opposite faces of A determined by the beginning and the end of \mathbf{a}_1 . The eigenvalues and eigenfunctions of (1) with the condition (3) are denoted by $\hat{\psi}_n(\hat{\mathbf{k}}; -\mathbf{a}_3)$ and $E_n(\hat{\mathbf{k}}; -\mathbf{a}_3)$, where $\hat{\mathbf{k}}$ is the two dimensional wavevector and $n = 0; 1; \dots$.

For the eigenvalues of two different eigenvalue problems defined by (2) and (3), we have the following theorem (See the Appendix):

$$\hat{\epsilon}_n(\hat{k}; \mathbf{x}_3) = \epsilon_n(\mathbf{k}); \quad \text{for } (\mathbf{k} - \hat{\mathbf{k}})_{\parallel} = 0; \quad i = 1, 2; \quad (4)$$

Eq. (4) is more or less like the Theorem 3.1.2 in [4] in the one dimensional case, but not as strong as the latter: No upper limit of $\hat{\epsilon}_n(\hat{k}; \mathbf{x}_3)$ is given except $\hat{\epsilon}_n(\hat{k}; \mathbf{x}_3) = \hat{\epsilon}_{n+1}(\hat{k}; \mathbf{x}_3)$.

Note in Eqs. (3) and (4), \mathbf{k} is a three dimensional wavevector and $\hat{\mathbf{k}}$ is a two dimensional wavevector. In Eq. (4) \mathbf{k} and $\hat{\mathbf{k}}$ have the same two dimensional wavevector in the \mathbf{lm} plane. For each energy band n and each $\hat{\mathbf{k}}$, there is one $\hat{\epsilon}_n(\hat{\mathbf{k}}; \mathbf{x}_3)$. Eq. (4) is true for any \mathbf{x}_3 , thus it indicates that in general a Bloch function $\psi_n(\mathbf{k}; \mathbf{x})$ does not have a "zero surface" $\mathbf{x}_3(\mathbf{x}_1; \mathbf{x}_2)$, except when it happens to be one of $\hat{\epsilon}_{n^0}(\hat{\mathbf{k}}; \mathbf{x}_3)$.

For the electronic states in a \mathbf{lm} with N_3 layers in the a_3 direction, we look for the the eigenvalues $\hat{\epsilon}$ and eigenfunctions $\hat{\psi}(\hat{\mathbf{k}}; \mathbf{x})$ of the following two equations:

$$\nabla^2 \hat{\psi}(\hat{\mathbf{k}}; \mathbf{x}) + [v(\mathbf{x}) - \hat{\epsilon}] \hat{\psi}(\hat{\mathbf{k}}; \mathbf{x}) = 0; \quad \text{if } \mathbf{x}_3 < \mathbf{x}_3 < \mathbf{x}_3 + N_3 \quad (5)$$

and

$$\hat{\psi}(\hat{\mathbf{k}}; \mathbf{x}) = 0; \quad \text{if } \mathbf{x}_3 = \mathbf{x}_3 \text{ or } \mathbf{x}_3 = \mathbf{x}_3 + N_3 \quad (6)$$

where $\mathbf{x}_3 = \mathbf{x}_3$ indicating the bottom of the \mathbf{lm} and N_3 is a positive integer indicating the \mathbf{lm} thickness. These electronic states $\hat{\psi}(\hat{\mathbf{k}}; \mathbf{x})$ are two dimensional Bloch waves in the \mathbf{lm} plane with additional index (es) indicating the component in the third direction.

One type of non-trivial solutions of (5) and (6) can be obtained from (3) by assigning

$$\begin{aligned} \hat{\psi}_n(\hat{\mathbf{k}}; \mathbf{x}_3) &= c_{N_3} \hat{\psi}_n(\hat{\mathbf{k}}; \mathbf{x}_3); & \text{if } \mathbf{x}_3 < \mathbf{x}_3 < \mathbf{x}_3 + N_3 \\ &= 0; & \text{if } \mathbf{x}_3 = \mathbf{x}_3 \text{ or } \mathbf{x}_3 = \mathbf{x}_3 + N_3 \end{aligned} \quad (7)$$

where c_{N_3} is a normalization constant. The corresponding eigenvalue $\hat{\epsilon}_n(\hat{\mathbf{k}}; \mathbf{x}_3) = \hat{\epsilon}_n(\hat{\mathbf{k}}; \mathbf{x}_3)$ is dependent on \mathbf{x}_3 but not on N_3 . A consequence of (4) is that for each energy band index n and each two dimensional wavevector $\hat{\mathbf{k}}$, there is one such solution (7) of Eqs. (5) and (6). We will further discuss this types of solutions later. Now we try to find out other solutions of (5) and (6).

The problem is simpler if the band structure of the crystal has the following symmetry

$$\epsilon_n(k_1b_1 + k_2b_2 + k_3b_3) = \epsilon_n(k_1b_1 + k_2b_2 - k_3b_3): \quad (8)$$

If this is the case, we note that

$$f_{n;k_1;k_2;k_3}(\mathbf{x}; z_3) = c_{n;k_1;k_2;k_3} \epsilon_n(k_1b_1 + k_2b_2 + k_3b_3; \mathbf{x}) + c_{n;k_1;k_2;-k_3} \epsilon_n(k_1b_1 + k_2b_2 - k_3b_3; \mathbf{x});$$

where $c_{n;k_1;k_2;k_3}$ and $c_{n;k_1;k_2;-k_3}$ are constant coefficients and are not zero, is a non-trivial solution of (5) due to (8). Non-trivial solutions of (5) and (6) can be obtained by assuming

$$\begin{aligned} \hat{\epsilon}_{n;j_3}(\hat{\mathbf{k}}; \mathbf{x}; z_3) &= f_{n;k_1;k_2;j_3}(\mathbf{x}; z_3) && \text{if } z_3 < x_3 < z_3 + N_3 \\ &= 0; && \text{if } x_3 \leq z_3 \text{ or } x_3 \geq z_3 + N_3 \end{aligned} \quad (9)$$

where $\hat{\mathbf{k}} = k_1\hat{b}_1 + k_2\hat{b}_2$, or $\hat{k}_1 = k_1$ and $\hat{k}_2 = k_2$, and

$$j_3 = j_3 - N_3; \quad j_3 = 1; 2; 3; \dots; N_3 - 1: \quad (10)$$

Here j_3 can be considered as a sub-band index. Because from (10) we have $e^{i z_3 N_3} e^{i z_3 N_3} = 0$, then we can always choose $c_{n;k_1;k_2;j_3}$ and $c_{n;k_1;k_2;-j_3}$ which are not zero to make [5] $f_{n;k_1;k_2;j_3}(x_1a_1 + x_2a_2 + z_3a_3) = f_{n;k_1;k_2;j_3}(x_1a_1 + x_2a_2 + (z_3 + N_3)a_3) = 0$: Therefore $\hat{\epsilon}_{n;j_3}(\hat{\mathbf{k}}; \mathbf{x}; z_3)$ defined in (9) are continuous functions satisfying (5) and (6) with eigenvalues given by

$$\hat{\epsilon}_{n;j_3}(k_1\hat{b}_1 + k_2\hat{b}_2) = \epsilon_n(k_1b_1 + k_2b_2 + j_3b_3) \quad (11)$$

Each eigenvalue $\hat{\epsilon}_{n;j_3}(\hat{\mathbf{k}})$ for this case, is a function of N_3 , the ϵ_{lm} thickness. But they all do not depend on the ϵ_{lm} boundary z_3 . The eigenvalues $\hat{\epsilon}_{n;j_3}(\hat{\mathbf{k}})$ of the electronic states in the ϵ_{lm} (11) map the band structure of the bulk $\epsilon_n(k_1b_1 + k_2b_2 + k_3b_3)$ exactly.

However, for many crystals such as important semiconductors with diamond structure or zinc-blend structure, in general (8) is not true. Thus we do not have (11) for general k_1 and k_2 . We have to treat each ϵ_{lm} case separately. In the following we treat FCC (001) ϵ_{lm} s and FCC (110) ϵ_{lm} s as two examples.

We discuss the FCC (001) ϵ_{lm} s first. The primitive vectors can be chosen as $a_1 = a/2(1; 1; 0)$ and $a_2 = a/2(1; 1; 0)$, $a_3 = a/2(1; 0; 1)$ and thus $b_1 = 1/a(1; 1; 1)$,

$b_2 = 1/a(1;1;-1)$, and $b_3 = 1/a(0;0;2)$. Three Cartesian components of the wavevector k can be obtained as $k_x = (k_1 + k_2)/a$, $k_y = (k_1 + k_2)/a$ and $k_z = (k_1 - k_2 + 2k_3)/a$.

In general, we do not have (8) for FCC crystals. Nevertheless, due to the high symmetry of the FCC band structures, we are still able to obtain an analytical expressions for the electronic states in FCC (001) Γ ns, similar to (11).

In fact, we can have many different ways to choose the primitive vectors. For example, we can choose a new primitive vector system as $a_1^0 = a_1$, $a_2^0 = a_2$, $a_3^0 = m_1 a_1 + m_2 a_2 + a_3$, here m_1 and m_2 are integers. The new primitive vectors in k space are $b_1^0 = b_1 - m_1 b_3$, $b_2^0 = b_2 - m_2 b_3$, $b_3^0 = b_3$. In principle, the primitive vector systems given by a_i and a_i^0 are equivalent. The wavevector k can be expressed as either $k_1 b_1 + k_2 b_2 + k_3 b_3$ or $k_1^0 b_1^0 + k_2^0 b_2^0 + k_3^0 b_3^0$ and $k_1 = k_1^0$, $k_2 = k_2^0$, $k_3 = m_1 k_1^0 + m_2 k_2^0 + k_3^0$. Thus for a specific wavevector k , in two different primitive vector systems used here, both k_1 and k_2 are unchanged.

In FCC (001) Γ ns we have $\hat{b}_1 = 1/a(1;-1;0)$ and $\hat{b}_2 = 1/a(1;1;0)$, $\hat{k}_1 = k_1$ and $\hat{k}_2 = k_2$. Our purpose is to find $\hat{\epsilon}_{n;j_3}(\hat{k})$ for different \hat{k} .

For FCC crystals we have $\epsilon_n(k_x; k_y; k_z) = \epsilon_n(k_x; k_y; k_z)$ for any k_x and k_y . We have also that $k_x = (k_1 + k_2)/a$, $k_y = (k_1 + k_2)/a$, $k_z = (k_1 - k_2 + 2k_3)/a = ((2m_1 + 1)k_1 - (2m_2 + 1)k_2 + 2k_3)/a$. If for two specific k_1 and k_2 , we can find two m_1 and m_2 , to make

$$(2m_1 + 1)k_1 + (2m_2 + 1)k_2 = 0; \quad (12)$$

then in the primitive vector system specifying by $a_3^0 = m_1 a_1 + m_2 a_2 + a_3$, we have

$$\epsilon_n(k_1 b_1^0 + k_2 b_2^0 + k_3^0 b_3^0) = \epsilon_n(k_1 b_1^0 + k_2 b_2^0 - k_3^0 b_3^0)$$

and thus

$$\hat{\epsilon}_{n;j_3}(k_1 \hat{b}_1 + k_2 \hat{b}_2) = \epsilon_n(k_1 b_1^0 + k_2 b_2^0 - k_3^0 b_3^0);$$

This in fact is [6]

$$\hat{\epsilon}_{n;j_3}(k_1 \hat{b}_1 + k_2 \hat{b}_2) = \epsilon_n(k_1 \hat{b}_1 + k_2 \hat{b}_2 + k_3 b_3); \quad (13)$$

where $k_3 = j - N_{j_3}$; $j_3 = 1; 2; \dots; N - 1$. Note (13) does not depend on m_1 and m_2 anymore.

There are some pairs of k_1 and k_2 for which the condition (12) can not be true. Nevertheless, in a small circle centered in an any specific pair k_1 and k_2 , there are always infinite number of pairs k_{1c} and k_{2c} , which can be as close to k_1 and k_2 as needed, for each pair we can find two integers m_1 and m_2 , to make $(2m_1 + 1)k_{1c} + (2m_2 + 1)k_{2c} = 0$. Thus (13) will be true for each such pair k_{1c} and k_{2c} . Because both $\hat{\psi}_{n;j_3}(k_1\hat{b}_1 + k_2\hat{b}_2)$ and $\psi_n(k_1\hat{b}_1 + k_2\hat{b}_2 + \frac{1}{2}b_3)$ are continuous functions of k_1 and k_2 , therefore (13) must be true for any k_1 and k_2 . The corresponding eigenfunction can be written as $\hat{\psi}_{n;j_3}(\hat{k}; \mathbf{x}; \frac{1}{2})$.

In the Cartesian system, Eq. (13) for (001) films can be written as:

$$\hat{\psi}_{n;j_3}(k_x; k_y) = \psi_n(k_x; k_y; 2\frac{1}{2}) \quad (14)$$

for any k_x and k_y , where $j_3 = j_3 \in \mathbb{N}_3$.

Eqs. (13) and (14) can be used for Si (001) films. Zhang and Zunger[7] calculated the electronic structure in thin Si (001) films using a pseudopotential method. Their results for the even number N_f of monolayer can be directly compared with our general analytical results: Our N_3 is equal to their $N_f=2$. Their "central observation" is that the energy spectrum of electronic states in Si quantum films ($N_f = 12$) maps the energy band structure of Si approximately. The equation (9) in [7], which Zhang and Zunger obtained from their numerical results, is a special case of Eq. (14) when $k_x = k_y = 0$. Therefore Eq. (14) is a more general result obtained analytically.

The FCC (110) films can be very similarly discussed.

The primitive vectors can be chosen as $a_1 = a(0;0;1)$ and $a_2 = a/2(1; 1;0)$, $a_3 = a/2(0;1;1)$. Correspondingly we have $b_1 = 1/a(-1; 1;1)$, $b_2 = 1/a(2;0;0)$, $b_3 = 1/a(2;2;0)$, and $\hat{b}_1 = 1/a(0;0;1)$, $\hat{b}_2 = 1/a(1; 1;0)$. By using very similar argument as we obtain Eq. (13) for FCC (001) films, but using that for FCC crystals $\psi_n(k_3 + k_2; k_3 - k_2; k_1) = \psi_n(k_3 + k_2; k_3 - k_2; k_1)$ is true for any k_1 and k_2 , we can obtain that for the electronic states in the N_3 layers of FCC (110) films, $\hat{\psi}_{n;j_3}(k_1\hat{b}_1 + k_2\hat{b}_2) = \psi_n(k_1\hat{b}_1 + k_2\hat{b}_2 + \frac{1}{2}b_3)$ for any k_1 and k_2 . Here $j_3 = j_3 \in \mathbb{N}_3$, j_3 is the sub-band index: $j_3 = 1;2;\dots;N_3 - 1$. This is exactly the same as Eq. (13). Thus Eq. (13) is correct for both FCC (001) films and FCC (110) films. The difference lies on that \hat{b}_1, \hat{b}_2 and b_3 are different in two cases. For FCC (110) films, Eq. (13) can also be written as

$$\hat{\psi}_{n;j_3}(k_1\hat{b}_1 + k_2\hat{b}_2) = \psi_n((2\frac{1}{2} - k_2)a; (2\frac{1}{2} + k_2)a; k_1a) \quad (15)$$

In the cases where $k_1 = k_2 = 0$, we have $\hat{\psi}_{n;j_3}(0) = \psi_n(j_3=N_3/2=a; j_3=N_3/2=a; 0)$. This is what Zhang and Zunger[7] obtained from their numerical results on Si (110) films due to that our N_3 is equal to their N_f in (110) films.

Much previous work also indicates that the eigenvalues of Bloch states in films map closely the dispersion relations of the unconfined Bloch waves[8]. Now we understand that the mapping in fact is general and exact in the cases treated here.

Franceschetti and Zunger[9] investigated the "X" transition in GaAs free standing (110) films, quantum wires and quantum dots. According to Eq. (15) we have analytically that for (110) films

$$E_{film} = \frac{\hbar^2}{2m} c(1=N_3/2=a; 1=N_3/2=a; 0); E_{film}^x = \frac{\hbar^2}{2m} c(1=N_3/2=a; 1=N_3/2=a; k_{min});$$

where c denotes the lowest conduction band, k_{min} is the location of the "X" valley on the k_z axis and N_3 is the number of mono-layers.

Each $\hat{\psi}_n(\hat{k}; x; j_3)$ defined in (7) is an electronic state in the film whose energy $\hat{E}_n(\hat{k}; j_3)$ is dependent on the film boundary j_3 but independent of the thickness of the film N_3 . In one-dimensional crystals of finite length [2] the energy bands $\psi_n(k)$ do not overlap and a k -dependent eigenvalue is either inside the band gap or at the band edge. In films the energy bands $\psi_n(k)$ usually overlap and $\hat{E}_n(\hat{k}; j_3)$ is either above or at the highest energy of the Bloch function with that n and that \hat{k} .

If in Eq. (4) $\hat{E}_n(\hat{k}; j_3) = \psi_n(k)$, $\hat{E}_n(\hat{k}; j_3)$ is equal to the highest energy for that energy band and that \hat{k} . It means that the corresponding eigenfunction of (3) $\hat{\psi}_n(\hat{k}; x)$ is a Bloch function $\psi_n(k; x)$. Examples of this case were observed, for example, in numerical results in the Fig. 3 and Fig. 4 of [7], such as the one of the double degenerated X_1 state in the valence band, the constant energy confined band edge state at the top of valence band, etc. Other examples are the constant energy confined band edge states at the top of the valence band observed in numerical calculations for Si (110) films[7] and GaAs (110) film [9] etc. This case happens when the corresponding Bloch function $\psi_n(k; x)$ with \hat{k} has a "zero surface" at $x_3 = j_3$ and thus has "zero surfaces" at $x_3 = j_3 + j$, where $j = 1; 2; \dots; N_3$.

In the cases where $\hat{E}_n(\hat{k}; j_3) > \psi_n(k)$; none of the Bloch function $\psi_n(k; x)$ with that n and that \hat{k} has a "zero surface" at $x_3 = j_3$. Then $\hat{\psi}_n(\hat{k}; x; j_3)$ could be a surface state. In

ideal one dimensional crystals of finite length we have proved that there is at most one surface state in each band gap [2]. Eq. (4) shows, there is at most one surface energy band $\hat{\epsilon}_n(\hat{k}; z)$ for each bulk energy band $\epsilon_n(k)$, even a film always has two surfaces. Nevertheless, due to that in three dimensional crystals below the major band gap there are several energy bands overlapping, such as the energy bands $n = 1; 2; 3$ in Si or GaAs etc, thus in the major band gap there could be more than one surface energy bands. However, for the band gap inside the valence band of III-V and II-VI semiconductors between the band $n = 0$ and the band $n = 1$, we predict that there is at most one surface energy band $\hat{\epsilon}_0(\hat{k}; z)$ for a perfectly even (001) or (110) film, as a direct consequence of Eq. (4).

In summary, we have demonstrated that for interesting free standing films, such as ideal FCC (001) films and FCC (110) films, exact and general results on the eigenvalues of the electronic states in the film can be obtained: For the film bounded between $z_3 a_3$ and $(N_3 + z_3) a_3$, there are $N_3 + 1$ electronic states $\hat{\epsilon}_{n;j_3}(\hat{k}; x; z)$ for each energy band n and each two dimensional wavevector \hat{k} , whose energy $\hat{\epsilon}_{n;j_3}(\hat{k})$ is dependent on the thickness of the film N_3 but not on the film boundary z_3 . The eigenvalues of these electronic states in the film map the energy bands $\epsilon_n(k)$ exactly; There is one electronic state $\hat{\epsilon}_n(\hat{k}; x; z)$ in the film for each n and \hat{k} whose energy $\hat{\epsilon}_n(\hat{k}; z)$ is dependent on the film boundary z_3 but not on the film thickness N_3 .

This approach can be further extended to obtain exact and general results on electronic states in quantum wires and quantum dots [10]. For example, it is found that for a quantum dot which are formed by FCC (001) or (110) films further truncated in two more directions and thus bounded between $x_1 a_1$ and $(x_1 + N_1) a_1$ and $x_2 a_2$ and $(x_2 + N_2) a_2$ and $z_3 a_3$ and $(z_3 + N_3) a_3$, for each energy band there are $(N_1 + 1)(N_2 + 1)(N_3 + 1)$ bulk states, $(N_1 + 1)(N_2 + 1) + (N_2 + 1)(N_3 + 1) + (N_3 + 1)(N_1 + 1)$ surface states, $(N_1 + 1) + (N_2 + 1) + (N_3 + 1)$ "side states" and one "corner state" in spite of that the crystal has six faces, twelve sides and eight corners.

Appendix

The Eq. (4) in the text is essentially an extension of the theorem (6.3.1) in [4] and its proof is similar, with some differences.

We choose $\varphi_n(\mathbf{k}; \mathbf{x})$ to be normalized over A : $\int_A \varphi_n(\mathbf{k}; \mathbf{x}) \varphi_n(\mathbf{k}; \mathbf{x}) d\mathbf{x} = 1$:

We denote F as the set of all complex-valued functions $f(\mathbf{x})$ which are continuous in A and have piecewise continuous first-order partial derivatives in A . The Dirichlet integral $J(f; g)$ in three dimensions is defined by

$$J(f; g) = \int_A \left(\nabla f(\mathbf{x}) \cdot \nabla g(\mathbf{x}) + v(\mathbf{x}) f(\mathbf{x}) g(\mathbf{x}) \right) d\mathbf{x} \quad (A.1)$$

for $f(\mathbf{x})$ and $g(\mathbf{x})$ in F . If in (A.1) $g(\mathbf{x})$ also has piecewise continuous second-order partial derivatives in A , from Green's theorem we have

$$J(f; g) = \int_A \left(f(\mathbf{x}) \nabla^2 g(\mathbf{x}) + v(\mathbf{x}) g(\mathbf{x}) \right) d\mathbf{x} + \int_{\partial A} f \frac{\partial g}{\partial n} dS; \quad (A.2)$$

where ∂A denotes the boundary of A , $\partial = \partial n$ denotes derivative along the outward normal to ∂A , and dS denotes an element of surface area of ∂A .

If $f(\mathbf{x})$ and $g(\mathbf{x})$ satisfy the conditions Eq. (2) in the text, the integral over ∂A is zero because the integrals over opposite faces of ∂A cancel out. In particular, when $g(\mathbf{x}) = \varphi_n(\mathbf{k}; \mathbf{x})$, (A.2) gives

$$J(f; g) = \varphi_n(\mathbf{k}) \int_A f(\mathbf{x}) \varphi_n(\mathbf{k}; \mathbf{x}) d\mathbf{x}.$$

Thus $J(\varphi_m(\mathbf{k}; \mathbf{x}); \varphi_n(\mathbf{k}; \mathbf{x})) = \varphi_n(\mathbf{k})$ if $m = n$ and $J(\varphi_m(\mathbf{k}; \mathbf{x}); \varphi_n(\mathbf{k}; \mathbf{x})) = 0$ if $m \neq n$.

Now we consider the function set $\hat{\varphi}(\hat{\mathbf{k}}; \mathbf{x}; \beta)$ which satisfy the conditions (3) in the text. We also choose $\hat{\varphi}(\hat{\mathbf{k}}; \mathbf{x}; \beta)$ to be normalized over A : $\int_A \hat{\varphi}(\hat{\mathbf{k}}; \mathbf{x}; \beta) \hat{\varphi}(\hat{\mathbf{k}}; \mathbf{x}; \beta) d\mathbf{x} = 1$.

Note if $f(\mathbf{x}) = \hat{\varphi}(\hat{\mathbf{k}}; \mathbf{x}; \beta)$, and $g(\mathbf{x}) = \varphi_n(\mathbf{k}; \mathbf{x})$, the integral over ∂A in (A.2) is also zero because the integral over two opposite faces of ∂A_1 and ∂A_2 cancel out due to that $(\mathbf{k} - \hat{\mathbf{k}})_{\hat{\mathbf{q}}} = 0$ for $i = 1, 2$ and the integral over each face of ∂A_3 is zero, due to that $f(\mathbf{x}) = 0$ when $\mathbf{x} \notin \partial A_3$.

Thus

$$J(\hat{\varphi}(\hat{\mathbf{k}}; \mathbf{x}; \beta); \varphi_n(\mathbf{k}; \mathbf{x})) = \varphi_n(\mathbf{k}) f_n(\mathbf{k})$$

where

$$f_n(k) = \int_A \hat{\psi}(k; x; \beta) \psi_n(k; x) dx;$$

and

$$\sum_{n=0}^{\infty} f_n(k)^2 = 1:$$

An important property of the function $\hat{\psi}(k; x; \beta)$ defined by (3) in the text is

$$J(\hat{\psi}(k; x; \beta); \hat{\psi}(k; x; \beta)) = \sum_{n=0}^{\infty} f_n(k) f_n(k)^2: \quad (A.3)$$

To prove (A.3), we assume $v(x) \geq 0$ first. Then $J(f; f) \geq 0$ from (A.1) for any f in F .

Thus for any positive integer N we have

$$J(\hat{\psi}(k; x; \beta) - \sum_{n=0}^N f_n(k) \psi_n(k; x); \hat{\psi}(k; x; \beta) - \sum_{n=0}^N f_n(k) \psi_n(k; x)) \geq 0:$$

That is

$$J(\hat{\psi}(k; x; \beta); \hat{\psi}(k; x; \beta)) - \sum_{n=0}^N f_n(k) f_n(k)^2:$$

N can be as large as it needs, therefore

$$J(\hat{\psi}(k; x; \beta); \hat{\psi}(k; x; \beta)) = \sum_{n=0}^{\infty} f_n(k) f_n(k)^2: \quad \text{if } v(x) \geq 0 \quad (A.4)$$

To prove (A.3) without the assumption that $v(x) \geq 0$, let v_0 be a constant which is sufficient large to make $v(x) + v_0 \geq 0$ in A . Then Eq. (1) in the text can be written as

$$r^2 y(x) + [V(x) - \lambda] y(x) = 0 \quad (A.5)$$

where $V(x) = v(x) + v_0$ and $\lambda = \lambda + v_0$. Since in (A.5) $V(x) \geq 0$, due to (A.4) we have

$$\int_A \hat{\psi}(k; x; \beta) \left(r^2 \hat{\psi}(k; x; \beta) + [v(x) + v_0] \hat{\psi}(k; x; \beta) - \lambda \hat{\psi}(k; x; \beta) \right) dx = \sum_{n=0}^{\infty} (f_n(k) + v_0) f_n(k)^2$$

That is

$$\int_A \hat{\psi}(k; x; \beta) \left(r^2 \hat{\psi}(k; x; \beta) + v(x) \hat{\psi}(k; x; \beta) - \lambda \hat{\psi}(k; x; \beta) \right) dx = \sum_{n=0}^{\infty} f_n(k) f_n(k)^2$$

This is (A :3). On the basis of (A :3) we can prove Eq. (4) in the text.

We consider

$$\hat{\varphi}(\hat{k}; \mathbf{x}; \mathbf{z}) = c_0 \hat{\varphi}_0(\hat{k}; \mathbf{x}; \mathbf{z}) + c_1 \hat{\varphi}_1(\hat{k}; \mathbf{x}; \mathbf{z}) + \dots + c_n \hat{\varphi}_n(\hat{k}; \mathbf{x}; \mathbf{z})$$

and choose $n + 1$ constants c_i to make

$$\sum_{i=0}^{X^n} \hat{\varphi}_i \hat{\varphi}_i = 1$$

and

$$f_i(\mathbf{k}) = \int_A \hat{\varphi}(\hat{k}; \mathbf{x}; \mathbf{z}) \hat{\varphi}_i(\mathbf{k}; \mathbf{x}) d\mathbf{x} = 0 \quad i = 0; 1; \dots; n-1 \quad (\text{A :6})$$

Eq. (A :6) corresponds to n homogeneous algebraic equations for $n + 1$ constants $c_0; c_1; \dots; c_n$.

A choice of such c_i s is always possible. Therefore

$$\hat{\varphi}_n(\hat{k}; \mathbf{z}) \sum_{i=0}^{X^n} \hat{\varphi}_i \hat{\varphi}_i(\hat{k}; \mathbf{z}) = J(\hat{\varphi}(\hat{k}; \mathbf{x}; \mathbf{z}); \hat{\varphi}(\hat{k}; \mathbf{x}; \mathbf{z}))$$

$$\sum_{i=0}^{X^1} f_i(\mathbf{k}) \hat{\varphi}_i(\mathbf{k}) = \sum_{i=n}^{X^1} f_i(\mathbf{k}) \hat{\varphi}_i(\mathbf{k}) \quad f_n(\mathbf{k}) \sum_{i=n}^{X^1} \hat{\varphi}_i(\mathbf{k}) \hat{\varphi}_i = f_n(\mathbf{k})$$

This is Eq. (4) in the text.

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 $= \nabla_n(k_1 \hat{b}_1 - k_1(2m_1 + 1)b_3 + k_2 \hat{b}_2 - k_2(2m_2 + 1)b_3 + k_3 b_3) = \nabla_n(k_1 \hat{b}_1 + k_2 \hat{b}_2 + k_3 b_3)$: E q. (12) i s u s e d i n t h e l a s t s t e p.
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